FAIRCHILD SEMICONDUCTOR®

July 2008

FDB150N10

N-Channel PowerTrench® MOSFET

100V, 57A, 15mΩ

Features

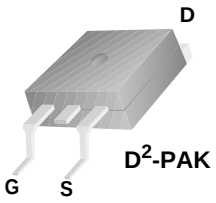
- $R_{DS(on)}$ = 12mΩ (Typ.) @ V_{GS} = 10V, I_D = 49A
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low $R_{DS(on)}$
- High power and current handling capability
- RoHS compliant

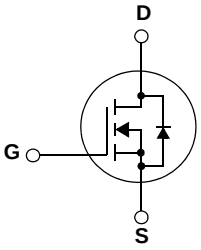
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC to DC convertors / Synchronous Rectification





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain to Source Voltage		100	V
V_{GSS}	Gate to Source Voltage		±20	V
I_D	Drain Current	-Continuous (T_C = 25°C)	57	A
		-Continuous (T_C = 100°C)	40	A
I_{DM}	Drain Current	- Pulsed (Note 1)	228	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	132	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.5	V/ns
P_D	Power Dissipation	(T_C = 25°C)	110	W
		- Derate above 25°C	0.88	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.13	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

Package Marking and Ordering Information $T_C = 25^oC$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB150N10	FDB150N10	D2-PAK	330mm	24mm	800

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V, T_C= 25°C	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	-	0.1	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 100V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 100V, V_{GS} = 0V, T_C = 150°C	-	-	500	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 49A	-	12	15	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20V, I_D = 49A (Note 4)	-	156	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V f = 1MHz	-	3580	4760	pF
C_{oss}	Output Capacitance		-	340	450	pF
C_{rss}	Reverse Transfer Capacitance		-	140	210	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50V, I_D = 49A V_{GS} = 10V, R_{GEN} = 25Ω (Note 4, 5)	-	47	104	ns
t_r	Turn-On Rise Time		-	164	338	ns
$t_{d(off)}$	Turn-Off Delay Time		-	86	182	ns
t_f	Turn-Off Fall Time		-	83	176	ns
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 80V, I_D = 49A V_{GS} = 10V (Note 4, 5)	-	53	69	nC
Q_{gs}	Gate to Source Gate Charge		-	19	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	15	-	nC
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	57	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	228	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 49A	-	-	1.3	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_{SD} = 49A dI_F/dt = 100A/μs (Note 4)	-	41	-	ns
Q_{rr}	Reverse Recovery Charge		-	70	-	nC

Notes:
1: Repetitive Rating: Pulse width limited by maximum junction temperature
2: L = 0.11mH, I_{AS} = 49A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3: I_{SD} ≤ 49A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4: Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5: Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

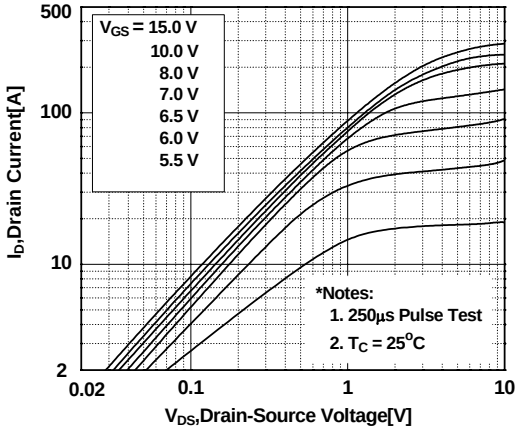


Figure 2. Transfer Characteristics

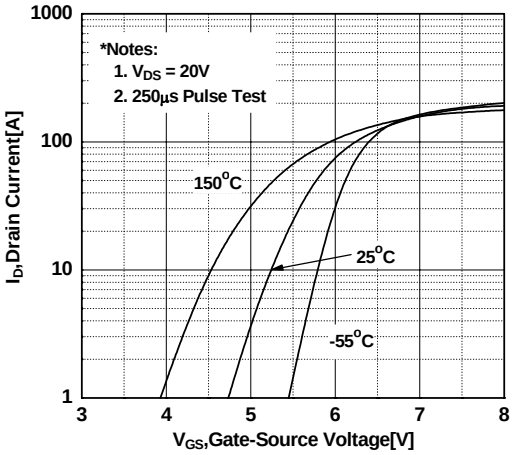


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

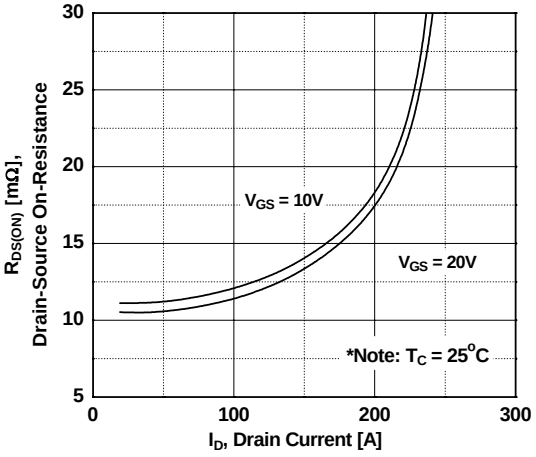


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

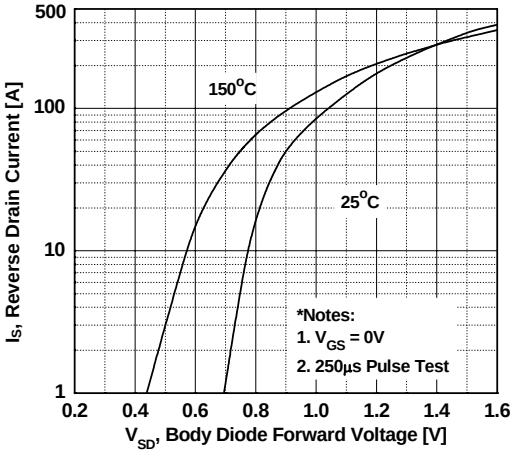


Figure 5. Capacitance Characteristics

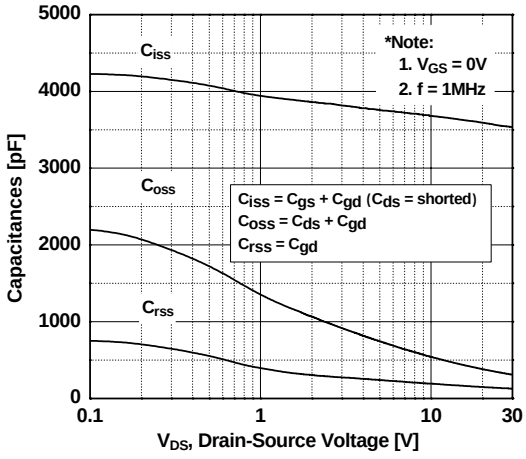
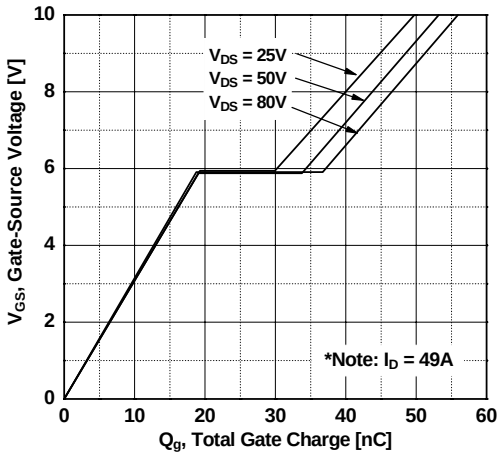


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

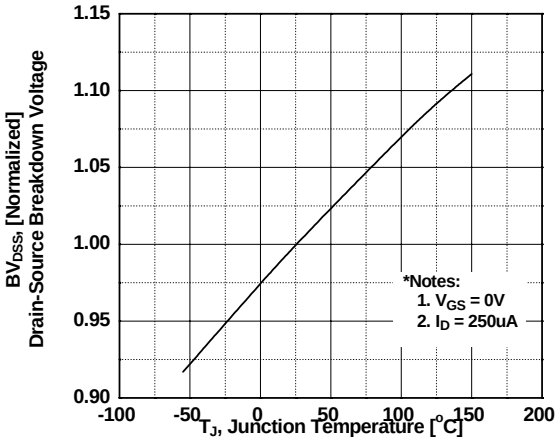


Figure 8. On-Resistance Variation vs. Temperature

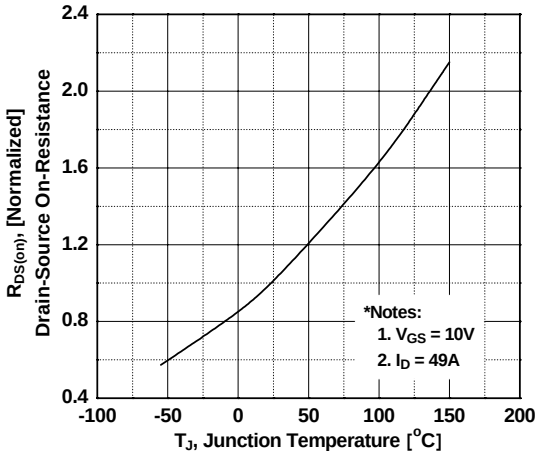


Figure 9. Maximum Safe Operating Area

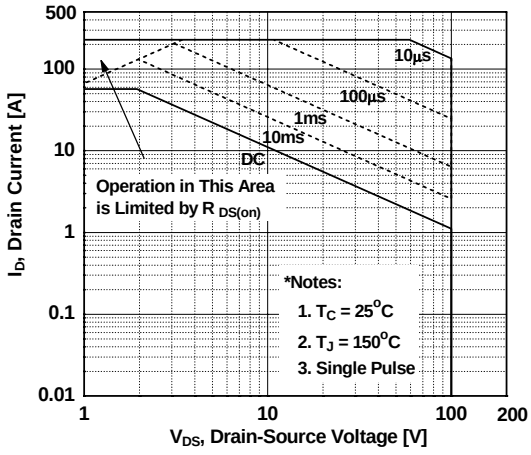


Figure 10. Maximum Drain Current vs. Case Temperature

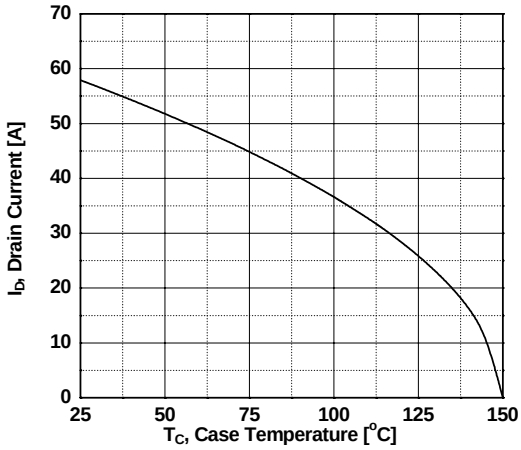
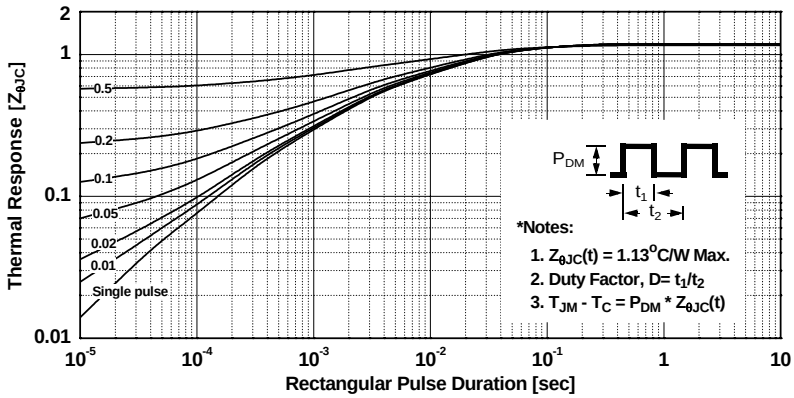
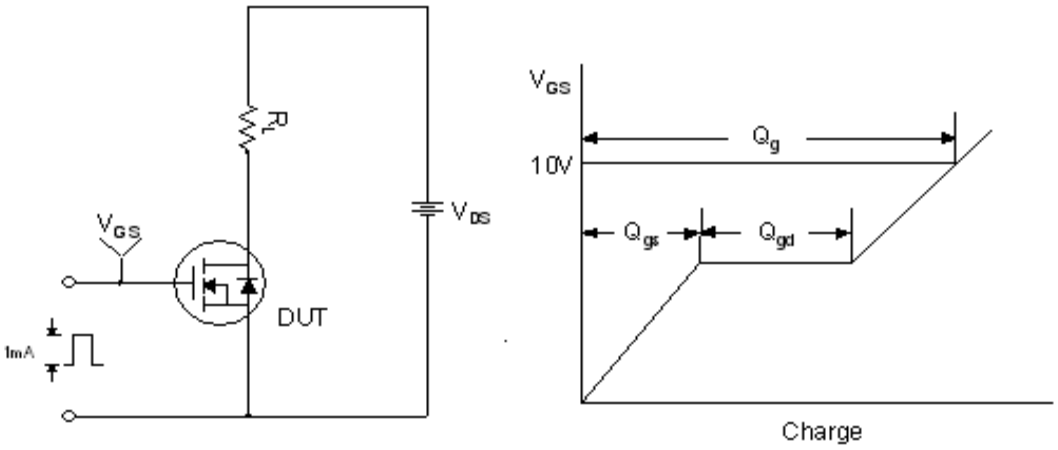


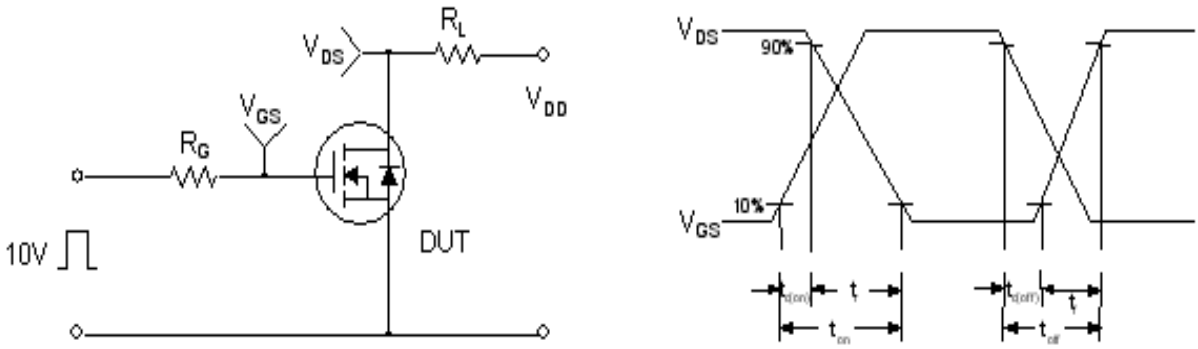
Figure 11. Transient Thermal Response Curve



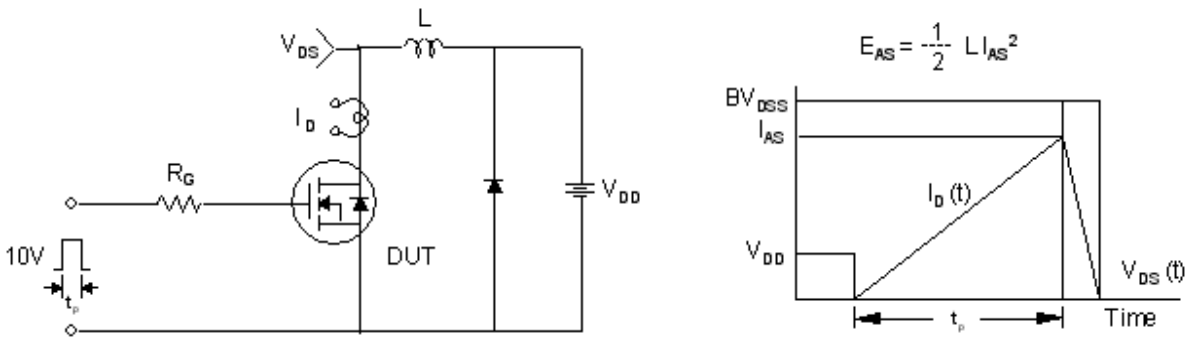
Gate Charge Test Circuit & Waveform



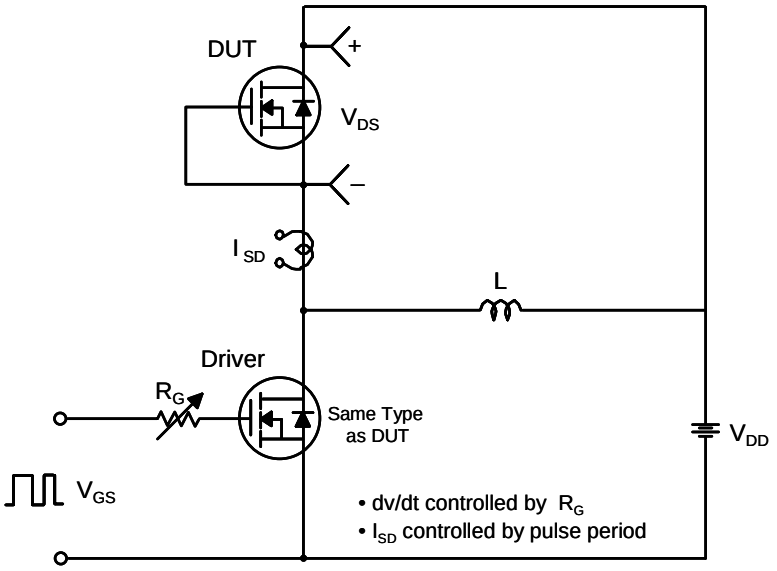
Resistive Switching Test Circuit & Waveforms

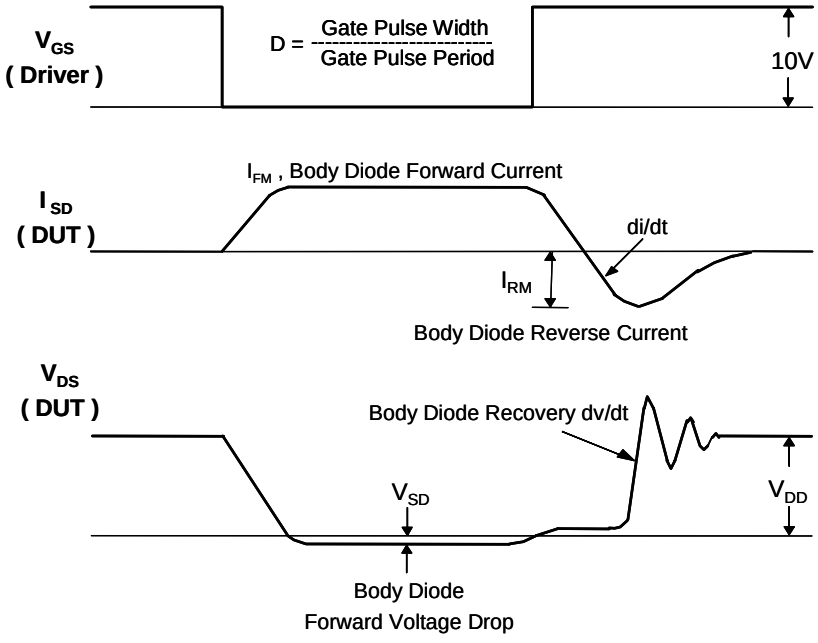


Unclamped Inductive Switching Test Circuit & Waveforms



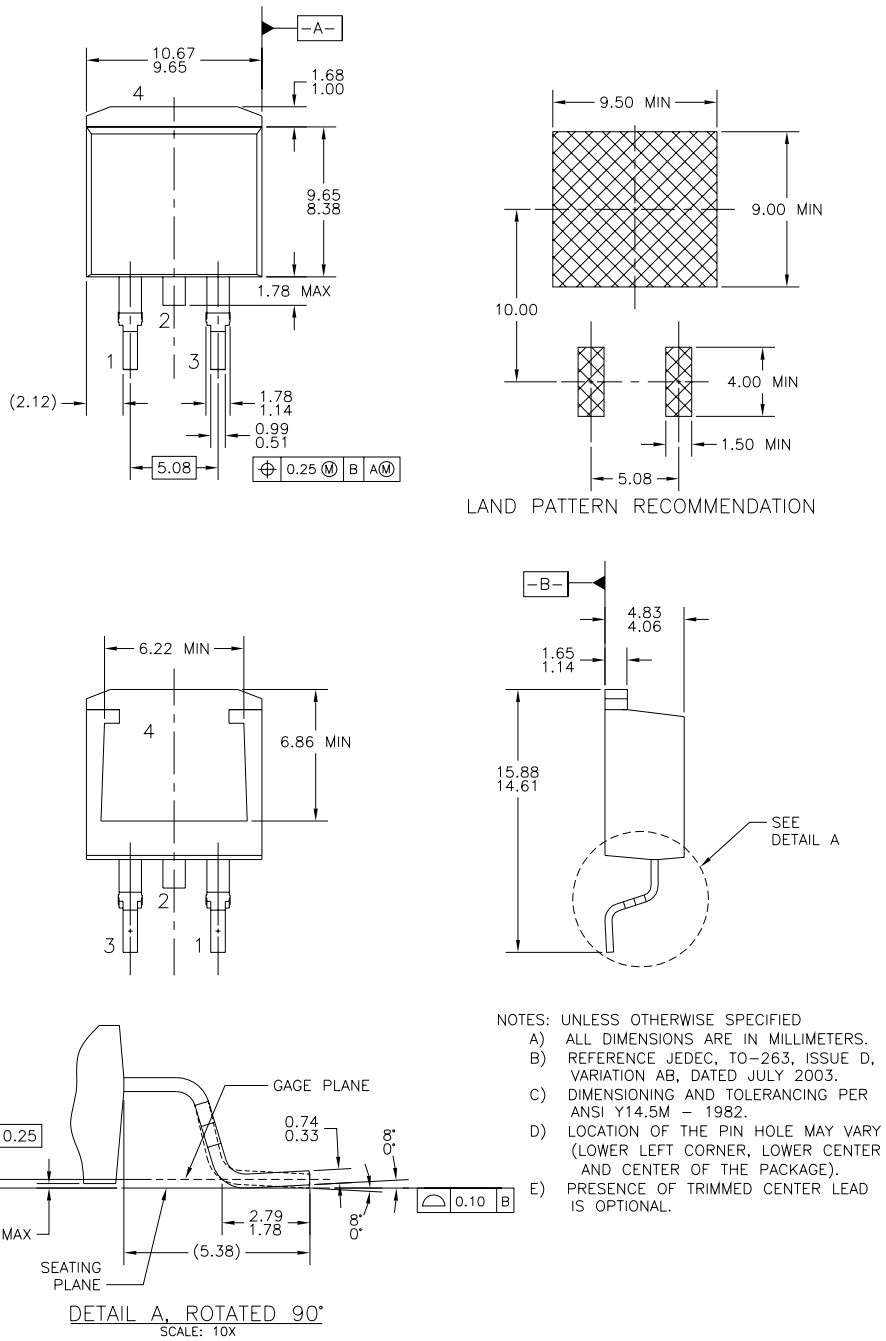
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

D2-PAK



NOTES: UNLESS OTHERWISE SPECIFIED

A) ALL DIMENSIONS ARE IN MILLIMETERS.

B) REFERENCE JEDEC, TO-263, ISSUE D, VARIATION AB, DATED JULY 2003.

C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5M – 1982.

D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).

E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.

Dimensions in Millimeters

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FACT®
FAST®
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FPS™
F-PFS™
FRFET®
Global Power Resource℠
Green FPS™
Green FPS™ e-Series™
GTO™
IntelliMAX™
ISOPLANAR™
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Datasheet Identification	Product Status	Definition
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Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	This datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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